

PTB 20078

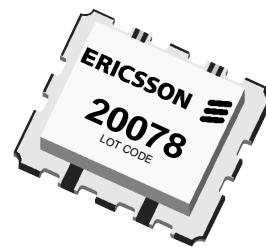
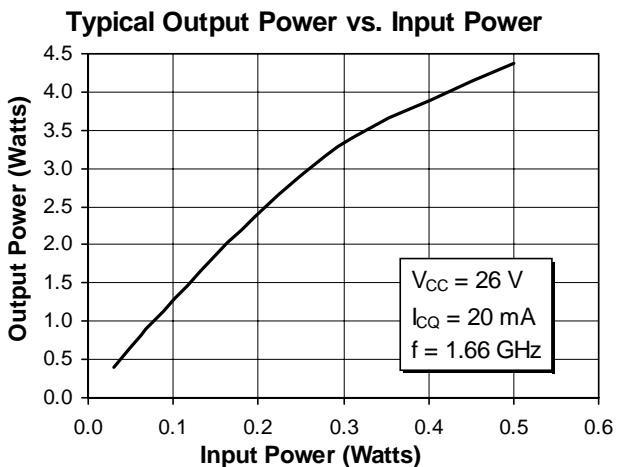
2.5 Watts, 1525–1660 MHz

INMARSAT RF Power Transistor

Description

The 20078 is a class AB, NPN, common emitter RF power transistor intended for 26 Vdc operation from 1525 to 1660 MHz. Rated at 2.5 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 2.5 Watts, 1525–1660 MHz
- Class AB Characteristics
- Gold Metallization
- Silicon Nitride Passivated
- Surface Mountable
- Available in Tape and Reel



Package 20227

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	50	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage (collector open)	V_{EBO}	4.0	Vdc
Collector Current (continuous)	I_C	0.5	Adc
Total Device Dissipation at $T_{flange} = 25^\circ\text{C}$ Above 25°C derate by	P_D	10.0 0.057	Watts W/ $^\circ\text{C}$
Storage Temperature	T_{stg}	150	$^\circ\text{C}$
Thermal Resistance ($T_{flange} = 70^\circ\text{C}$)	$R_{\theta JC}$	17.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics (100% Tested)

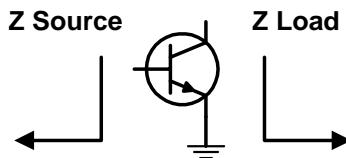
Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$V_{BE} = 0 \text{ V}$, $I_C = 5 \text{ mA}$	$V_{(BR)CES}$	50	—	—	Volts
Breakdown Voltage C to E	$I_B = 0 \text{ A}$, $I_C = 10 \text{ mA}$, $R_{BE} = 22 \Omega$	$V_{(BR)CER}$	50	—	—	Volts
Breakdown Voltage E to B	$I_C = 0 \text{ A}$, $I_E = 5 \text{ mA}$	$V_{(BR)EBO}$	4	5	—	Volts
DC Current Gain	$V_{CE} = 5 \text{ V}$, $I_C = 250 \text{ mA}$	h_{FE}	20	40	—	—

RF Specifications (100% Tested)

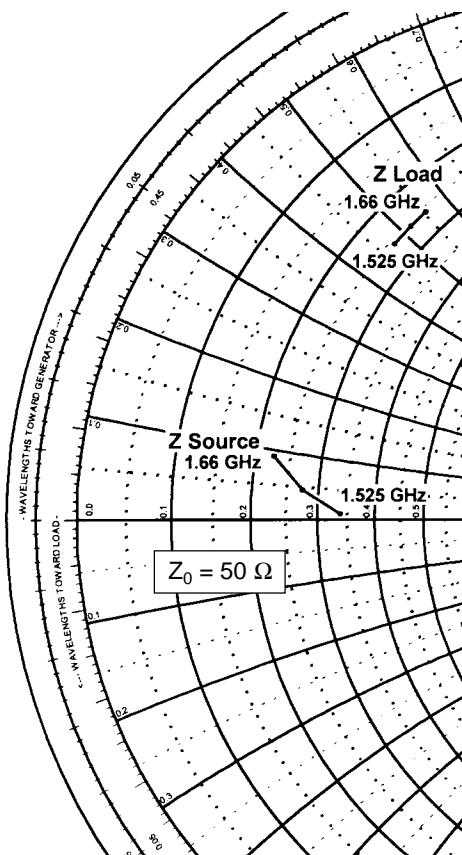
Characteristic	Symbol	Min	Typ	Max	Units
Gain $(V_{CC} = 26 \text{ Vdc}, P_{out} = 1.0 \text{ W}, I_{CQ} = 20 \text{ mA}, f = 1.525; 1.66 \text{ GHz})$	G_{pe}	9	11.0	—	dB
Power Out at 1 dB Compression $(V_{CC} = 26 \text{ Vdc}, I_{CQ} = 20 \text{ mA}, f = 1.525; 1.66 \text{ GHz})$	P_{-1dB}	2.5	3.5	—	Watts
Load Mismatch Tolerance $(V_{CC} = 26 \text{ Vdc}, P_{out} = 2.5 \text{ W}, I_{CQ} = 20 \text{ mA}, f = 1.660 \text{ GHz—all phase angles at frequency of test})$	Ψ	—	—	5:1	—

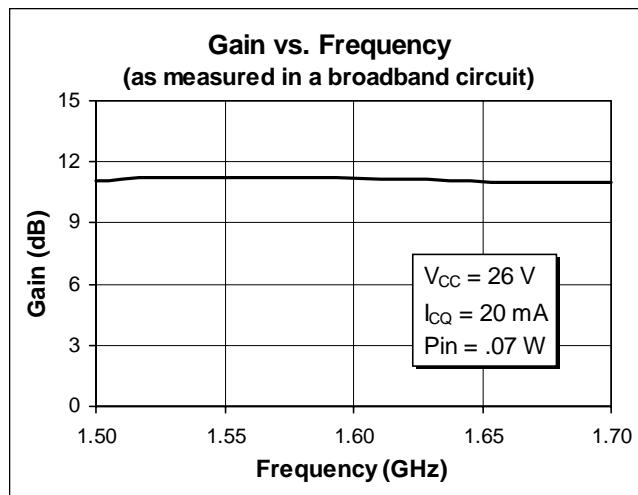
Impedance Data (data shown for fixed-tuned broadband circuit)

$(V_{CC} = 26 \text{ Vdc}, P_{out} = 2.5 \text{ W}, I_{CQ} = 20 \text{ mA})$



Frequency	Z Source		Z Load	
GHz	R	jX	R	jX
1.525	16.9	0.5	12.9	23.8
1.593	13.7	2.3	12.9	25.9
1.660	11.3	4.6	12.9	27.7



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